

# Week 2 Practice Assignment

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# Week 2 Practice Assignment

Poll Q1. Can intrinsic silicon fermi energy ( $E_{Fi}$ ) ever be exactly at the center of the bandgap ( $\frac{E_g}{2}$ ) ?

- A. Never
- B. For  $T=0$  K
- C. For  $m_e^* = m_h^*$
- D. Insufficient data

$$E_{Fi} - E_V = \frac{E_g}{2} - \frac{3kT}{4} \ln \left( \frac{m_e^*}{m_h^*} \right)$$

Poll Q2. For intrinsic silicon what would affect conductivity?

- A. temperature
- B.  $\mu_e$  and  $\mu_h$
- C. Both A and B
- D. Neither A nor B

$$\sigma = ne\mu_e + pe\mu_h$$



# Week 2 Practice Assignment

1) In an **intrinsic semiconductor**,  $N_c > N_v$ . Where is the **Fermi level** located at room temperature? Take  $E_g$  as the band gap. All choices are given with respect to the top of the valence band ( $E_v$ ).

- above  $E_g/2$
- below  $E_g/2$
- at  $E_g/2$
- at  $E_g$

$$E_{Fi} = E_V + \frac{E_g}{2} - \frac{kT}{2} \ln \left( \frac{N_C}{N_V} \right)$$

$$E_{Fi} = 0 + \frac{E_g}{2} - \frac{kT}{2} \ln(A)$$

$$E_{Fi} = \frac{E_g}{2} - (B)$$

$$E_{Fi} < \frac{E_g}{2}$$

Since  $N_c > N_v$

$$A > 1$$

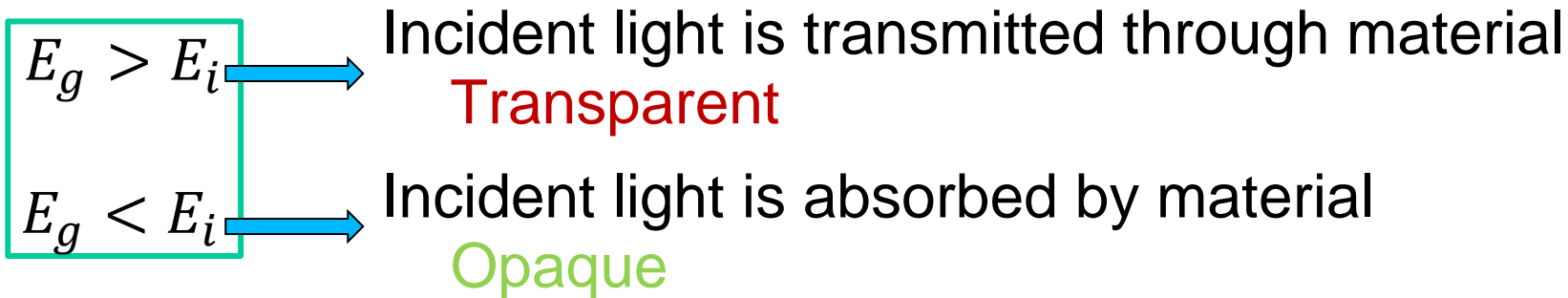
$$B > 0$$



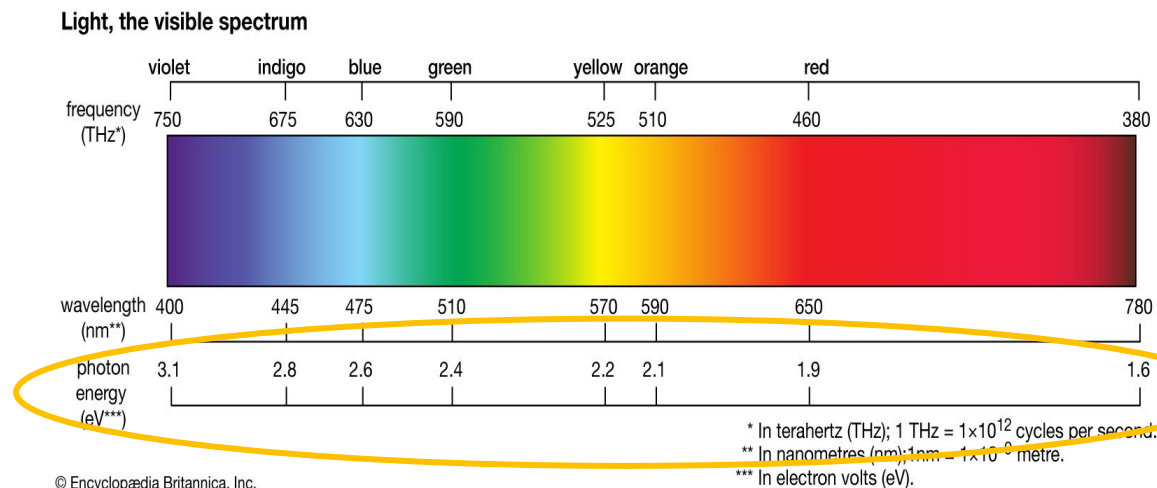
# Week 2 Practice Assignment

2) Which of the following materials can be considered **transparent** to visible light?

- Silica
- Silicon
- Cadmium sulphide
- Gallium arsenide



Material	Band gap $E_g$ (eV)
SiO <sub>2</sub>	9
Si	1.1
CdS <sub>2</sub>	2.4
GaAs	1.4



# Week 2 Practice Assignment

3) Given that the effective masses of electrons and holes in silicon are  $1.10 m_e$  and  $0.55 m_e$  respectively, find the location of the **intrinsic Fermi level** at 300 K.  $m_e$  is the rest mass of an electron and the band gap of silicon is 1.1 eV. Give your answer in eV.

- 0.54 eV above the valence band edge
- 0.54 eV below the conduction band edge
- 0.45 eV above the valence band edge
- 0.45 eV above the conduction band edge

Given:  $m_e^* = 1.1m_e$  and  $m_h^* = 0.55 m_e$  ,  $E_g = 1.1$  eV

$$E_{Fi} = E_V + \frac{E_g}{2} - \frac{3kT}{4} \ln \left( \frac{m_e^*}{m_h^*} \right)$$

$$E_{Fi} = 0 + \frac{1.1}{2} - \frac{3kT}{4} \ln \left( \frac{1.1m_e}{0.55m_e} \right)$$

$$E_{Fi} = 0 + 0.55 - 0.014$$

$$E_{Fi} = 0.54 \text{ eV}$$



# Week 2 Practice Assignment

4) Two semiconductors X and Y have the **same effective density of states** both at the conduction ( $N_c$ ) and valence band edges ( $N_v$ ). The **1 point** intrinsic carrier concentration of X and Y at 300 K are  $2 \times 10^{13} \text{ cm}^{-3}$  and  $10^{10} \text{ cm}^{-3}$  respectively. If the band gap of X is 0.7 eV, find the band gap of Y (in eV).

- 1.4
- 1.1
- 0.9
- 0.7

Given:  $N_{Cx} = N_{Cy}$ ,  $N_{Vx} = N_{Vy}$ ,  $n_{ix} = 2 \times 10^{13} \text{ cm}^{-3}$ ,  $n_{iy} = 10^{10} \text{ cm}^{-3}$ ,  $E_{gX} = 0.7 \text{ eV}$

$$n_i = \sqrt{N_V N_C} \times e^{\left(\frac{-E_g}{2kT}\right)}$$

$$n_{iX} = \sqrt{N_{VX} N_{CX}} \times e^{\left(\frac{-E_{gX}}{2kT}\right)}$$

$$n_{iY} = \sqrt{N_{VY} N_{CY}} \times e^{\left(\frac{-E_{gY}}{2kT}\right)}$$

$$\frac{n_{iX}}{n_{iY}} = \frac{\sqrt{N_{VX} N_{CX}} \times e^{\left(\frac{-E_{gX}}{2kT}\right)}}{\sqrt{N_{VY} N_{CY}} \times e^{\left(\frac{-E_{gY}}{2kT}\right)}}$$

$$2 \times 10^3 = e^{\left(\frac{E_{gY} - E_{gX}}{2kT}\right)}$$



# Week 2 Practice Assignment

4) Two semiconductors X and Y have the **same effective density of states** both at the conduction ( $N_c$ ) and valence band edges ( $N_v$ ). The **1 point** intrinsic carrier concentration of X and Y at 300 K are  $2 \times 10^{13} \text{ cm}^{-3}$  and  $10^{10} \text{ cm}^{-3}$  respectively. If the band gap of X is 0.7 eV, find the band gap of Y (in eV).

1.4

1.1

0.9

0.7

$$2 \times 10^3 = e^{\left(\frac{E_{gY} - E_{gX}}{2kT}\right)}$$

$$7.6 = \frac{E_{gY} - 0.7}{2kT}$$

$$7.6 = \frac{E_{gY} - 0.7}{2 \times 0.026}$$

$$0.395 = E_{gY} - 0.7$$

$$E_{gY} = 1.1 \text{ eV}$$



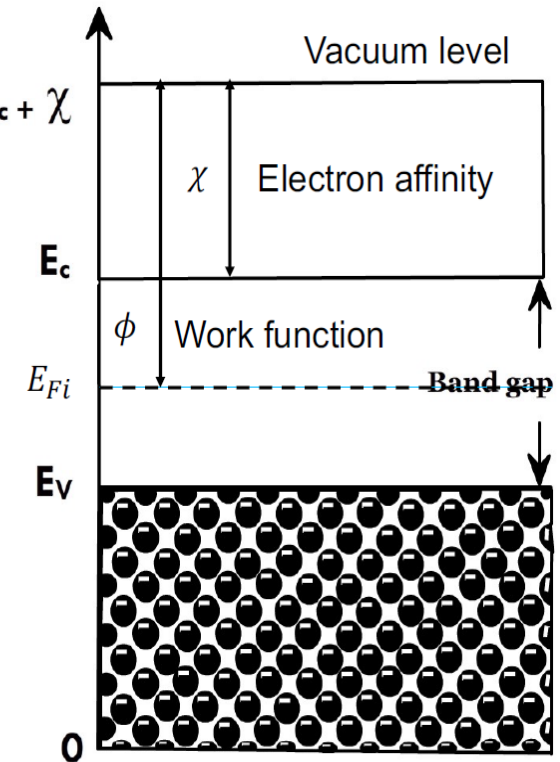
# Week 2 Practice Assignment

5) The band gap of intrinsic GaAs is 1.43 eV and its electron affinity is 4.07 eV. Assuming that the effective masses of electrons and holes at the band edges are **equal**, what is the **work function** of the material? Give your answer in eV.

- 2.64
- 5.5
- 4.07
- 4.78

Conduction  
band

Valence  
band



Given:  $E_g = 1.43 \text{ eV}$  ,  $\chi = 4.07 \text{ eV}$  ,  $m_h^* = m_e^*$

$$\phi = \chi + E_C - E_{Fi}$$

$$E_{Fi} - E_V = \frac{E_g}{2} - \frac{3kT}{4} \ln \left( \frac{m_e^*}{m_h^*} \right)$$

$$\phi = \chi + E_C - \left[ E_V + \frac{E_g}{2} - \frac{3kT}{4} \ln \left( \frac{m_e^*}{m_h^*} \right) \right]$$

$$\phi = \chi + E_C - \left[ 0 + \frac{E_g}{2} - 0 \right]$$

$$\phi = \chi + E_C - \left[ \frac{E_g}{2} \right]$$

$$\phi = \chi + \frac{E_g}{2}$$

$$\phi = 4.78 \text{ eV}$$

